

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1-3. (Canceled)

4. (Currently Amended) A group III nitride compound semiconductor comprising:
- a substrate;
 - a buffer layer formed on said substrate into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern such that substrate-exposed portions are formed in a scattered manner;
 - a first group III nitride compound semiconductor layer $Al_{x1}Ga_{y1}In_{1-x1-y1}N$, wherein $0 \leq x1 \leq 1$, $0 \leq y1 \leq 1$, $0 \leq x1 + y1 \leq 1$, formed on said buffer layer;
 - a second group III nitride compound semiconductor layer $Al_{x2}Ga_{y2}In_{1-x2-y2}N$, wherein $0 \leq x2 \leq 1$, $0 \leq y2 \leq 1$, $0 \leq x2 + y2 \leq 1$, which causes epitaxial growth from at least an island of said first group III nitride compound semiconductor serving as nuclei so that said second group III nitride compound semiconductor keeps a an empty gap to said substrate-exposed portions and connects adjacent ones of said first group III nitride compound semiconductor; and
 - a device layer made of gallium nitride group compound semiconductor formed on said second group III nitride compound semiconductor layer.
5. (Currently Amended) A group III nitride compound semiconductor comprising:
- a substrate;
 - a buffer layer formed on said substrate into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern such that substrate-exposed portions are formed in a scattered manner;
 - a first group III nitride compound semiconductor layer $Al_{x1}Ga_{y1}In_{1-x1-y1}N$, wherein $0 \leq x1 \leq 1$, $0 \leq y1 \leq 1$, $0 \leq x1 + y1 \leq 1$, formed on said buffer layer; and
 - a second group III nitride compound semiconductor layer $Al_{x2}Ga_{y2}In_{1-x2-y2}N$, wherein $0 \leq x2 \leq 1$, $0 \leq y2 \leq 1$, $0 \leq x2 + y2 \leq 1$, which causes epitaxial growth from at least an island of said first group III nitride compound semiconductor serving as nuclei so that said second group III nitride compound semiconductor keeps a an empty gap to said substrate-exposed portions and

connects adjacent ones of said first group III nitride compound semiconductor,

wherein said first group III nitride compound semiconductor layer is formed into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern by etching.

6. (Previously Presented) A group III nitride compound semiconductor according to claim 4, wherein said first group III nitride compound semiconductor layer is formed into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern by etching.

7. (Currently Amended) A group III nitride compound semiconductor comprising:
a substrate;

a buffer layer formed on said substrate into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern such that substrate-exposed portions are formed in a scattered manner;

a first group III nitride compound semiconductor layer $Al_{x1}Ga_{y1}In_{1-x1-y1}N$, wherein $0 \leq x1 \leq 1$, $0 \leq y1 \leq 1$, $0 \leq x1 + y1 \leq 1$, formed on said buffer layer; and

a second group III nitride compound semiconductor layer $Al_{x2}Ga_{y2}In_{1-x2-y2}N$, wherein $0 \leq x2 \leq 1$, $0 \leq y2 \leq 1$, $0 \leq x2 + y2 \leq 1$, which causes epitaxial growth from at least an island of said first group III nitride compound semiconductor serving as nuclei so that said second group III nitride compound semiconductor keeps a an empty gap to said substrate-exposed portions and connects adjacent ones of said first group III nitride compound semiconductor,

wherein said second group III nitride compound semiconductor layer is formed by lateral growth above said substrate-exposed portions.

8. (Previously Presented) A group III nitride compound semiconductor according to claim 4, wherein said second group III nitride compound semiconductor layer is formed by lateral growth above said substrate-exposed portions.

9. (Currently Amended) A group III nitride compound semiconductor comprising:
a substrate;

a buffer layer formed on said substrate into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern such that substrate-exposed portions are formed in a scattered manner;

a first group III nitride compound semiconductor layer $Al_{x1}Ga_{y1}In_{1-x1-y1}N$, wherein $0 \leq x1 \leq 1$, $0 \leq y1 \leq 1$, $0 \leq x1 + y1 \leq 1$, formed on said buffer layer; and

a second group III nitride compound semiconductor layer $Al_{x2}Ga_{y2}In_{1-x2-y2}N$, wherein $0 \leq x2 \leq 1$, $0 \leq y2 \leq 1$, $0 \leq x2 + y2 \leq 1$, which causes epitaxial growth from at least an island of said first group III nitride compound semiconductor serving as nuclei so that said second group III nitride compound semiconductor keeps a an empty gap to said substrate-exposed portions and connects adjacent ones of said first group III nitride compound semiconductor,

wherein said substrate comprises at least one of sapphire, silicon, and silicon carbide.

10. (Previously Presented) A group III nitride compound semiconductor according to claim 4, wherein said substrate comprises at least one of sapphire, silicon, and silicon carbide.

11. (Currently Amended) A group III nitride compound semiconductor comprising:

a substrate;

a buffer layer formed on said substrate into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern such that substrate-exposed portions are formed in a scattered manner;

a first group III nitride compound semiconductor layer $Al_{x1}Ga_{y1}In_{1-x1-y1}N$, wherein $0 \leq x1 \leq 1$, $0 \leq y1 \leq 1$, $0 \leq x1 + y1 \leq 1$, formed on said buffer layer; and

a second group III nitride compound semiconductor layer $Al_{x2}Ga_{y2}In_{1-x2-y2}N$, wherein $0 \leq x2 \leq 1$, $0 \leq y2 \leq 1$, $0 \leq x2 + y2 \leq 1$, which causes epitaxial growth from at least an island of said first group III nitride compound semiconductor serving as nuclei so that said second group III nitride compound semiconductor keeps a an empty gap to said substrate-exposed portions and connects adjacent ones of said first group III nitride compound semiconductor,

wherein said buffer layer comprises at least one of $Al_{x3}Ga_{1-x3}N$, wherein $0 \leq x3 \leq 1$, and $Al_{x4}Ga_{y4}In_{1-x4-y4}N$, wherein $0 \leq x4 \leq 1$, $0 \leq y4 \leq 1$, $0 \leq x4 + y4 \leq 1$, having an arbitrary composition ratio.

12. (Currently Amended) A group III nitride compound semiconductor comprising:

a substrate;

a buffer layer formed on said substrate into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern such that substrate-exposed portions are formed in a scattered manner;

a first group III nitride compound semiconductor layer $Al_{x1}Ga_{y1}In_{1-x1-y1}N$, wherein $0 \leq x1 \leq 1$, $0 \leq y1 \leq 1$, $0 \leq x1+y1 \leq 1$, formed on said buffer layer; and

a second group III nitride compound semiconductor layer $Al_{x2}Ga_{y2}In_{1-x2-y2}N$, wherein $0 \leq x2 \leq 1$, $0 \leq y2 \leq 1$, $0 \leq x2+y2 \leq 1$, which causes epitaxial growth from at least an island of said first group III nitride compound semiconductor serving as nuclei so that said second group III nitride compound semiconductor keeps a an empty gap to said substrate-exposed portions and connects adjacent ones of said first group III nitride compound semiconductor,

wherein said first group III nitride compound semiconductor layer and said second group III nitride compound semiconductor layer comprise a same composition ratio.

13. (Previously Presented) A group III nitride compound semiconductor according to claim 4, wherein said first group III nitride compound semiconductor layer and said second group III nitride compound semiconductor layer comprise a same composition ratio.

14. (Currently Amended) A group III nitride compound semiconductor comprising:
a substrate;

a buffer layer formed on said substrate into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern such that substrate-exposed portions are formed in a scattered manner;

a first group III nitride compound semiconductor layer $Al_{x1}Ga_{y1}In_{1-x1-y1}N$, wherein $0 \leq x1 \leq 1$, $0 \leq y1 \leq 1$, $0 \leq x1+y1 \leq 1$, formed on said buffer layer; and

a second group III nitride compound semiconductor layer $Al_{x2}Ga_{y2}In_{1-x2-y2}N$, wherein $0 \leq x2 \leq 1$, $0 \leq y2 \leq 1$, $0 \leq x2+y2 \leq 1$, which causes epitaxial growth from at least an island of said first group III nitride compound semiconductor serving as nuclei so that said second group III nitride compound semiconductor keeps a an empty gap to said substrate-exposed portions and connects adjacent ones of said first group III nitride compound semiconductor,

wherein said first group III nitride compound semiconductor layer comprises a thickness of 500 Å to 2000 Å.

15. (Previously Presented) A group III nitride compound semiconductor according to claim 4, wherein said first group III nitride compound semiconductor layer comprises a thickness of 500 Å to 2000 Å.

16. (Currently Amended) A group III nitride compound semiconductor comprising:
a substrate;

a buffer layer formed on said substrate into an island pattern comprising any of a dot pattern, a striped pattern, and a grid pattern such that substrate-exposed portions are formed in a scattered manner;

a first group III nitride compound semiconductor layer $Al_{x1}Ga_{y1}In_{1-x1-y1}N$, wherein $0 \leq x1 \leq 1$, $0 \leq y1 \leq 1$, $0 \leq x1 + y1 \leq 1$, formed on said buffer layer; and

a second group III nitride compound semiconductor layer $Al_{x2}Ga_{y2}In_{1-x2-y2}N$, wherein $0 \leq x2 \leq 1$, $0 \leq y2 \leq 1$, $0 \leq x2 + y2 \leq 1$, which causes epitaxial growth from at least an island of said first group III nitride compound semiconductor serving as nuclei so that said second group III nitride compound semiconductor keeps a an empty gap to said substrate-exposed portions and connects adjacent ones of said first group III nitride compound semiconductor,

wherein said substrate-exposed portions are wider than said first group III nitride compound semiconductor layer formed in an island pattern.

17. (Previously Presented) A group III nitride compound semiconductor, according to claim 4, wherein said substrate-exposed portions are wider than said first group III nitride compound semiconductor layer formed in an island pattern.

18-57. (Canceled)

58. (Currently Amended) The group III nitride compound semiconductor, according to claim 4, wherein said substrate-exposed portions comprise a width thickness that is greater than a width thickness of a region above said first group III nitride compound semiconductor layer.

59. (Currently Amended) The group III nitride compound semiconductor, according to claim 58, wherein said width thickness of said substrate-exposed portions comprises a

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thickness of $1\mu\text{m}$ to $10\mu\text{m}$.

60. (Currently Amended) The group III nitride compound semiconductor, according to claim 58, wherein said width ~~thickness~~ of said region above said first group III nitride compound semiconductor layer comprises a width ~~thickness~~ of $1\mu\text{m}$ to $10\mu\text{m}$.

61. (New) The group III nitride compound semiconductor, according to claim 4, wherein said second group III nitride compound semiconductor does not contact said substrate.